REMARKS

Claims 1, 3-5, 17, 31 and 32 have been amended, and claim 37 has been added. No new matter has been added by virtue of the amendments. For instance, support for the amendments appears in the original claims.

Claims 1-5 were rejected under 35 U.S.C. 102(e) over Fujishiro et al. (U.S. Patent 6,495299). The rejection is traversed.

Independent claim 1 call for a method that includes exposing an applied photoresist layer to radiation having a wavelength less than 300 nm.

Fujishiro et al. does not disclose a method. Among other things, Fujishiro et al. is specifically directed to longer wavelength exposure. See, for instance, Fujishiro et al. at column 12, lines 54-57, where the wavelength range 300-400 nm is reported. At column 8, lines 52-55, 365 nm is reported.

Accordingly, the rejection should be withdrawn. See, for instance, *In re Marshall*, 198 USPQ at 346 ("[r]ejections under 35 USC 102 are proper only when the claimed subject matter is identically disclosed or described in the prior art.").

Claims 1-15, 17, 18, 31-33, 35 and 36 were rejected under 35 U.S.C. 103 over Malik (U.S. Patent 6,133,412) in view of Pawlowski (U.S. Patent 6,277,750). As grounds for the rejection, the following is stated (Office Action at page 4):

> Malik discloses ketones rather than aldehydes and is silent with respect to acetals.
>
> Pawlowski teaches the requivalence of aldehydes and ketones in the reaction in a photoresist which results in the formation of acetals (col. 8, lines 30-40).

The rejection is traversed.

Among other things, Pawlowski is **not** directed to photoresists as indicated in the Office Action , but instead to bottom anti-reflective coating materials over which a photoresist layer is applied. See, for example, Pawlowksi at column 11, line 43 through column 12, line 8.

That Pawlowski bottom anti-reflective coating layer is not photo-patterned, but rather crosslinked through the entire layer. Thus, Pawlowksi reports the following at column 11, lines 43-51 (emphasis added):

> The process of the present invention further comprises coating a substrate with the bottom antireflective coating of the present invention and heating on a hotplate or convection over at sufficiently high temperature for a sufficient length of time to remove the solvent in the coating and **to crosslink the polymer** to a sufficient extent so as not to be soluble in the coating solvent of the photoresist or in the alkaline developer.

Respectfully, contrary to the position advance in the Office Action, the skilled worker would not have had any particular incentive to look to features of a crosslinked, non-developed bottom layer material for incorporation into a photoresist where patterning and development is required.

In view thereof, reconsideration and withdrawal of the rejection are requested.

Claim 16 was rejected under 35 U.S.C. 103 over Park (U.S. Patent 5916995). The rejection is traversed.

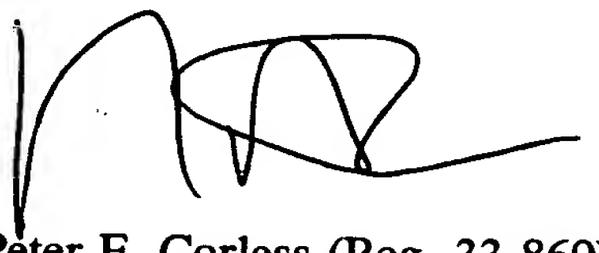
Independent claim 17 calls for a positive photoresist composition.

The Park document is specifically directed to negative-acting compositions. No incentive or expectation of success would have existed to attempt to modify the composition reported by Park to render it positive-working.

In view thereof, withdrawal of the rejection is requested.

It is believed the application is in condition for immediate allowance, which action is earnestly solicited.

Respectfully submitted,



Peter F. Corless (Reg. 33,860)
EDWARDS & ANGELL, LLP
P.O. Box 9169
Boston, MA 02209
(617) 439-4444